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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Annex A: Measurement data and plots

A.1 Spectrum analyser plots: CW, 80%AM, GSM and CDMA signals



0 Hz Span CW Plot (835MHz)

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0 Hz Span 80% AM Plot (835MHz)

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0 Hz Span GSM (835MHz)

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Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

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0 Hz Span CW Plot (1880MHz)

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W



0 Hz Span 80% AM Plot (1880MHz)

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RIM Testing Services	Report for the Black	Berry® Smartphone model R	CF71CW	6 (180)
Author Data Daoud Attayi	Dates of Test Mar 20-24, 2009	Report No RTS-1528-0903-38 Rev 1	FCC ID L6ARCF70C	W



0 Hz Span GSM (1880MHz)

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Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W
•				



0 Hz Span CW Plot (835MHz)

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Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W



0 Hz Span 80% AM Plot (835MHz)

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W
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0 Hz Span CDMA (835MHz)

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	d Compatibility RF Emissio rry® Smartphone model R0	ns Test CF71CW	Page 10 (180)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

1.3 ms		RBH 3 MHz	Narker 1 CT1 3 10.86 dBa	SILLER
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0 Hz Span CW Plot (1880MHz)

RTS RIM Testing Services	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCF71CW			Page 11 (180)
Author Data Daoud Attayi	Dates of Test Report No FCC ID Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W



0 Hz Span 80% AM Plot (1880MHz)

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0 Hz Span CDMA (1880MHz)

RTS RIM Testing Services	Annex A to Hearing Ai Report for the BlackBe	d Compatibility RF Emissio erry® Smartphone model R0	ons Test CF71CW	Page 13 (180)
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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W

A.2 Dipole validation and probe modulation factor plots

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 24/03/2009 12:57:06 PM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_CW835_20.00dBm.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 103.3 V/m; Power Drift = 0.000 dB Maximum value of Total (measured) = 168.4 V/m

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 169.7 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 103.3 V/m; Power Drift = 0.000 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
158.7 M4	166.5 M4	164.5 M4
Grid 4	Grid 5	Grid 6
88.1 M4	90.2 M4	87.4 M4
Grid 7	Grid 8	Grid 9
161.8 M4	169.7 M4	164.5 M4

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W



 $0 \; dB = 169.7 V/m$

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W

Date/Time: 20/03/2009 4:33:39 PM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_CW835_PMF_GSM.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 110.3 V/m; Power Drift = 0.103 dB Maximum value of Total (measured) = 182.7 V/m

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Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009	W		

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 185.3 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 110.3 V/m; Power Drift = 0.103 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
159.9 M4	166.9 M4	165.0 M4
Grid 4	Grid 5	Grid 6
91.2 M4	93.8 M4	91.0 M4
Grid 7	Grid 8	Grid 9
175.2 M4	185.3 M4	178.8 M4

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70CV			W



 $0 \ dB = 185.3 \ V/m$

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W

Date/Time: 20/03/2009 4:51:53 PM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_AM835_PMF_GSM.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 76.9 V/m; Power Drift = -0.027 dB Maximum value of Total (measured) = 124.3 V/m

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	d Compatibility RF Emissio rry® Smartphone model R0	ns Test CF71CW	Page 21 (180)
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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 126.0 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 76.9 V/m; Power Drift = -0.027 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
110.2 M4	114.5 M4	113.7 M4
Grid 4	Grid 5	Grid 6
64.0 M4	65.3 M4	63.4 M4
Grid 7	Grid 8	Grid 9
119.4 M4	126.0 M4	121.9 M4

RIM Testing Services	DocumentPageAnnex A to Hearing Aid Compatibility RF Emissions Test22 (180)Report for the BlackBerry® Smartphone model RCF71CW22 (180)			Page 22 (180)
Author Data Dates o Daoud Attayi Man	of Test Report N r 20-24, 2009 RTS-	1528-0903-38 Rev 1	FCC ID L6ARCF70C	W
dB 0.000 -2.68 -5.36 -8.04 -10.7				

 $0 \ dB = 126.0 V/m$

Date/Time: 20/03/2009 4:17:25 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_GSM835.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: GSM 850; Frequency: 835 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 37.6 V/m; Power Drift = 0.127 dB Maximum value of Total (measured) = 62.4 V/m

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 63.2 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 37.6 V/m; Power Drift = 0.127 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

	, ,	
Grid 1	Grid 2	Grid 3
53.7 M4	56.9 M4	56.5 M4
Grid 4	Grid 5	Grid 6
30.9 M4	31.9 M4	31.1 M4
Grid 7	Grid 8	Grid 9
59.8 M4	63.2 M4	60.1 M4

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dB 0.000 -2.80 -5.60				
-8.40				
-11.2				
-14.0				

 $0 \ dB = 63.2 V/m$

Date/Time: 20/03/2009 4:43:42 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CW835_PMF_CDMA.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 39.6 V/m; Power Drift = 0.000 dB Maximum value of Total (measured) = 65.1 V/m

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1):

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Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 65.9 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 39.6 V/m; Power Drift = 0.000 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

I cuit 12 mora m	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	
Grid 1	Grid 2	Grid 3
57.5 M4	60.8 M4	60.2 M4
Grid 4	Grid 5	Grid 6
33.0 M4	34.1 M4	33.1 M4
Grid 7	Grid 8	Grid 9
62.1 M4	65.9 M4	63.2 M4

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 $0 \, dB = 65.9 \, V/m$

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 20/03/2009 5:01:10 PM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_AM835_PMF_CDMA.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 25.8 V/m; Power Drift = -0.097 dB Maximum value of Total (measured) = 42.0 V/m

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Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 42.5 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 25.8 V/m; Power Drift = -0.097 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
37.1 M4	39.0 M4	38.9 M4
Grid 4	Grid 5	Grid 6
21.3 M4	21.7 M4	21.4 M4
Grid 7	Grid 8	Grid 9
40 3 M4	42 5 M4	40 9 M4

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Author Data Daoud Attayi	Dates of Test Mar 20-24, 2009	Report No RTS-1528-0903-38 Rev 1	FCC ID L6ARCF7()CW
dB 0.000 -2.70 -5.40				
-8.10				
-10.8				
-13.5		48		

 $0 \ dB = 42.5 V/m$

Date/Time: 20/03/2009 4:07:44 PM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_CDMA835.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CDMA 800; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 41.2 V/m; Power Drift = -0.033 dB Maximum value of Total (measured) = 68.6 V/m

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 69.0 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 41.2 V/m; Power Drift = -0.033 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
59.0 M4	62.4 M4	61.8 M4
Grid 4	Grid 5	Grid 6
33.6 M4	34.8 M4	33.8 M4
Grid 7	Grid 8	Grid 9

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W



 $0 \, dB = 69.0 \, V/m$

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 24/03/2009 1:10:29 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CW1880_20.00dBm.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 150.0 V/m; Power Drift = -0.118 dB Maximum value of Total (measured) = 129.2 V/m

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 130.9 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 150.0 V/m; Power Drift = -0.118 dB

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

Grid 1	Grid 2	Grid 3		
120.6 M2	127.3 M2	125.6 M2		
Grid 4	Grid 5	Grid 6		
86.7 M3	91.2 M3	89.0 M3		
Grid 7	Grid 8	Grid 9		
122.4 M2	130.9 M2	129.7 M2		
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 $0 \ dB = 130.9 V/m$

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W

Date/Time: 20/03/2009 3:12:30 PM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_CW1880_PMF_GSM.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 107.4 V/m; Power Drift = -0.077 dB Maximum value of Total (measured) = 92.8 V/m

E Scan - measurement distance from the probe sensor center to

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CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 93.8 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 107.4 V/m; Power Drift = -0.077 dB

Hearing Aid Near-Field Category: M3 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
84.5 M3	88.2 M3	87.4 M3
Grid 4	Grid 5	Grid 6
61.4 M4	63.6 M3	62.5 M4
Grid 7	Grid 8	Grid 9

Peak E-field in V/m

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 $0 \ dB = 93.8 V/m$

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W

Date/Time: 20/03/2009 3:25:36 PM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_AM_1880_PMF_GSM.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 67.7 V/m; Power Drift = -0.011 dB Maximum value of Total (measured) = 59.2 V/m

E Scan - measurement distance from the probe sensor center to

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CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 59.8 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 67.7 V/m; Power Drift = -0.011 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
52.9 M4	55.4 M4	54.7 M4
Grid 4	Grid 5	Grid 6
38.8 M4	40.4 M4	39.5 M4
Grid 7	Grid 8	Grid 9

Peak E-field in V/m

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 $0 \ dB = 59.8 V/m$

Date/Time: 20/03/2009 2:51:56 PM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_GSM1880.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 36.2 V/m; Power Drift = -0.009 dB Maximum value of Total (measured) = 31.6 V/m

E Scan - measurement distance from the probe sensor center to

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CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 32.1 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 36.2 V/m; Power Drift = -0.009 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
28.2 M4	29.6 M4	29.3 M4
Grid 4	Grid 5	Grid 6
20.7 M4	21.5 M4	21.0 M4
Grid 7	Grid 8	Grid 9
30.2 M4	32.1 M4	31.5 M4

Peak E-field in V/m

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70CV			W

Date/Time: 20/03/2009 3:19:28 PM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_CW1880_PMF_CDMA.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 53.6 V/m; Power Drift = -0.164 dB Maximum value of Total (measured) = 45.9 V/m

E Scan - measurement distance from the probe sensor center to

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CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 46.5 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 53.6 V/m; Power Drift = -0.164 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
41.4 M4	43.3 M4	42.6 M4
Grid 4	Grid 5	Grid 6
30.3 M4	31.4 M4	30.4 M4
Grid 7	Grid 8	Grid 9
43.7 M4	46.5 M4	45.6 M4

Peak E-field in V/m

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 $0 \ dB = 46.5 V/m$

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70CV			W

Date/Time: 20/03/2009 3:32:28 PM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_AM_1880_PMF_CDMA.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 34.1 V/m; Power Drift = -0.073 dB Maximum value of Total (measured) = 29.7 V/m

E Scan - measurement distance from the probe sensor center to

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70CV			W

CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 30.1 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 34.1 V/m; Power Drift = -0.073 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
26.7 M4	28.0 M4	27.7 M4
Grid 4	Grid 5	Grid 6
19.5 M4	20.2 M4	19.8 M4
Grid 7	Grid 8	Grid 9
28.4 M4	30.1 M4	29.6 M4

Peak E-field in V/m

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 $0 \ dB = 30.1 \ V/m$

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70CV			W

Date/Time: 20/03/2009 3:00:38 PM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_CDMA1880.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CDMA 1900; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 53.3 V/m; Power Drift = -0.133 dB Maximum value of Total (measured) = 45.9 V/m

E Scan - measurement distance from the probe sensor center to

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CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 46.5 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 53.3 V/m; Power Drift = -0.133 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
40.9 M4	42.8 M4	42.5 M4
Grid 4	Grid 5	Grid 6
30.1 M4	31.4 M4	30.3 M4
Grid 7	Grid 8	Grid 9
43.9 M4	46.5 M4	45.8 M4

Peak E-field in V/m

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W



 $0 \ dB = 46.5 V/m$

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Date/Time: 24/03/2009 12:16:40 PM

Test Laboratory: RTS File Name: HAC_H_Dipole_CW835_20.00dBm.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8

Build 184

H Scan - measurement distance from the probe sensor center to

CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1):

Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.508 A/m; Power Drift = 0.028 dB

Maximum value of Total (measured) = 0.479 A/m

H Scan - measurement distance from the probe sensor center to

CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.481 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.508 A/m; Power Drift = 0.028 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m	
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Grid 1	Grid 2	Grid 3
0.429 M4	0.472 M4	0.463 M4
Grid 4	Grid 5	Grid 6
0.444 M4	0.481 M4	0.469 M4
Grid 7	Grid 8	Grid 9
0.444 M4	0.479 M4	0.462 M4

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0 dB = 0.481 A/m

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Date/Time: 20/03/2009 5:14:23 PM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_CW835_PMF_GSM.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.524 A/m; Power Drift = 0.149 dB Maximum value of Total (measured) = 0.497 A/m

H Scan - measurement distance from the probe sensor center to

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CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.499 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.524 A/m; Power Drift = 0.149 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.436 M4	0.478 M4	0.473 M4
Grid 4	Grid 5	Grid 6
0.455 M4	0.499 M4	0.482 M4
Grid 7 0.455 M4	Grid 8 0.496 M4	Grid 9 0.478 M4

Peak H-field in A/m

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Date/Time: 20/03/2009 5:21:57 PM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_AM835_PMF_GSM.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.376 A/m; Power Drift = -0.095 dB Maximum value of Total (measured) = 0.348 A/m

H Scan - measurement distance from the probe sensor center to

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.349 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.376 A/m; Power Drift = -0.095 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/n	n
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Grid 1	Grid 2	Grid 3
0.310 M4	0.339 M4	0.333 M4
Grid 4	Grid 5	Grid 6
0.320 M4	0.349 M4	0.339 M4

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W



0 dB = 0.349 A/m

Date/Time: 20/03/2009 5:34:34 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_GSM835.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: GSM 850; Frequency: 835 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.191 A/m; Power Drift = 0.021 dB Maximum value of Total (measured) = 0.179 A/m

H Scan - measurement distance from the probe sensor center to

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CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.179 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.191 A/m; Power Drift = 0.021 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Grid 1	Grid 2	Grid 3	
0.159 M4	0.174 M4	0.169 M4	
Grid 4	Grid 5	Grid 6	
0.163 M4	0.179 M4	0.173 M4	
Grid 7 0.163 M4	Grid 8 0.179 M4	Grid 9 0.170 M4	

Peak H-field in A/m

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W



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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 20/03/2009 5:18:22 PM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_CW835_PMF_CDMA.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.186 A/m; Power Drift = -0.009 dB Maximum value of Total (measured) = 0.174 A/m

H Scan - measurement distance from the probe sensor center to

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CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.175 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.186 A/m; Power Drift = -0.009 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.156 M4	0.169 M4	0.167 M4
Grid 4	Grid 5	Grid 6
0.162 M4	0.175 M4	0.170 M4
Grid 7	Grid 8	Grid 9
0.162 M4	0.174 M4	0.168 M4

Peak H-field in A/m

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 $0 \ dB = 0.175 \mbox{A/m}$

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 20/03/2009 5:25:07 PM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_AM835_PMF_CDMA.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.122 A/m; Power Drift = 0.059 dB Maximum value of Total (measured) = 0.115 A/m

H Scan - measurement distance from the probe sensor center to

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CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.115 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.122 A/m; Power Drift = 0.059 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

	¥/ 111	
Grid 1	Grid 2	Grid 3
0.103 M4	0.112 M4	0.110 M4
Grid 4	Grid 5	Grid 6
0.106 M4	0.115 M4	0.112 M4
Grid 7	Grid 8	Grid 9
0.106 M4	0.114 M4	0.110 M4

Peak H-field in A/m
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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W



 $0 \ dB = 0.115 \ A/m$

Date/Time: 20/03/2009 5:42:12 PM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_CDMA835.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CDMA 800; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.200 A/m; Power Drift = -0.161 dB Maximum value of Total (measured) = 0.186 A/m

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70CV			W

CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.187 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.200 A/m; Power Drift = -0.161 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.169 M4	0.181 M4	0.178 M4
Grid 4	Grid 5	Grid 6
0.173 M4	0.187 M4	0.181 M4
Grid 7	Grid 8	Grid 9
0.173 M4	0.185 M4	0.181 M4

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 $0 \ dB = 0.187 \text{A/m}$

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W

Date/Time: 24/03/2009 12:01:46 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_CW1880_20.00dBm.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.505 A/m; Power Drift = -0.016 dB Maximum value of Total (measured) = 0.475 A/m

CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.477 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.505 A/m; Power Drift = -0.016 dB

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.413 M2	0.454 M2	0.445 M2
Grid 4	Grid 5	Grid 6
0.439 M2	0.477 M2	0.465 M2
Grid 7	Grid 8	Grid 9
0.422 M2	0.460 M2	0.445 M2

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 $0 \ dB = 0.477 \text{A/m}$

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70CV			W

Date/Time: 24/03/2009 11:05:55 AM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_CW1880_PMF_GSM.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.349 A/m; Power Drift = 0.016 dB Maximum value of Total (measured) = 0.326 A/m

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CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.328 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.349 A/m; Power Drift = 0.016 dB

Hearing Aid Near-Field Category: M3 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.285 M3	0.315 M3	0.308 M3
Grid 4	Grid 5	Grid 6
0.303 M3	0.328 M3	0.320 M3
Grid 7	Grid 8	Grid 9
0.294 M3	0.317 M3	0.309 M3

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0 dB = 0.328 A/m

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W

Date/Time: 24/03/2009 11:33:20 AM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_AM1880_PMF_GSM.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: AM 80%; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.223 A/m; Power Drift = 0.136 dB Maximum value of Total (measured) = 0.211 A/m

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CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.212 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.223 A/m; Power Drift = 0.136 dB

Hearing Aid Near-Field Category: M3 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.181 M4	0.203 M3	0.197 M3
Grid 4	Grid 5	Grid 6
0.193 M3	0.212 M3	0.206 M3
Grid 7	Grid 8	Grid 9
0.188 M4	0.204 M3	0.197 M3

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 $0 \ dB = 0.212 A/m$

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W

Date/Time: 24/03/2009 10:40:43 AM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_GSM1880.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.139 A/m; Power Drift = -0.054 dB Maximum value of Total (measured) = 0.129 A/m

CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.129 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.139 A/m; Power Drift = -0.054 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
0.107 M4	0.121 M4	0.117 M4
Grid 4	Grid 5	Grid 6
0.115 M4	0.129 M4	0.124 M4
Grid 7	Grid 8	Grid 9
0.112 M4	0.125 M4	0.119 M4

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0 dB = 0.129 A/m

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W

Date/Time: 24/03/2009 11:15:36 AM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_CW1880_PMF_CDMA.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.172 A/m; Power Drift = -0.013 dB Maximum value of Total (measured) = 0.162 A/m

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CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.162 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.172 A/m; Power Drift = -0.013 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.140 M4	0.154 M4	0.151 M4
Grid 4	Grid 5	Grid 6
0.149 M4	0.162 M4	0.158 M4
Grid 7	Grid 8	Grid 9
0.145 M4	0.157 M4	0.152 M4

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0 dB = 0.162 A/m

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Date/Time: 24/03/2009 11:43:27 AM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_AM1880_PMF_CDMA.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: AM 80%; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.111 A/m; Power Drift = -0.115 dB Maximum value of Total (measured) = 0.103 A/m

CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.104 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.111 A/m; Power Drift = -0.115 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

/111	
Grid 2	Grid 3
0.099 M4	0.097 M4
Grid 5	Grid 6
0.104 M4	0.102 M4
Grid 8	Grid 9
ona o	
0.101 M4	0.098 M4
	Grid 2 0.099 M4 Grid 5 0.104 M4 Grid 8 0.101 M4

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0 dB = 0.104 A/m

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Date/Time: 24/03/2009 10:56:34 AM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_CDMA1880.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CDMA 1900; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, -6.30 mm Reference Value = 0.179 A/m; Power Drift = 0.001 dB Maximum value of Total (measured) = 0.168 A/m

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CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.169 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.179 A/m; Power Drift = 0.001 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.143 M4	0.160 M4	0.156 M4
Grid 4	Grid 5	Grid 6
0.153 M4	0.169 M4	0.165 M4
Grid 7	Grid 8	Grid 9
0.150 M4	0.163 M4	0.157 M4

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0 dB = 0.169 A/m

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Justification of Step Size and Interpolation

This section demonstrates that a 5mm step size with interpolation provides sufficient resolution for RF emissions measurements. The DASY 4 uses interpolation algorithms to derive 9 interpolated points between every measured point.



The figure above shows the raw measured field strength perpendicular to the length of the validation dipole. The TCB guidance slides require the 3dB width to be much larger than the step size. The width between -3dB points is ≥ 21 mm, at least 4 times the step size.



This figure shows the interpolated field strength perpendicular to the dipole. The interpolated points follow the raw points with no inconsistencies.

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The green line in this figure shows the axis along which the points lie.

Comparison of 5mm and 2mm step sizes

An additional set of measurements was taken: dipole validations were performed using 5mm and 2mm step sizes. The delta between the two readings is insignificant for both field types (< 0.4% for E and 0% for H), demonstrating that 5mm is sufficient. The plots follow.

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Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m³ Phantom section: H Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of Total (measured) = 134.8 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm Maximum value of Total field (slot averaged) = 131.0 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

E in V/m (Time averaged) E in V/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
123.2	138.1	138.4	123.2	138.1	138.4
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
80.9	92.3	92.2	80.9	92.3	92.2
Grid 7	Grid 8	Grid 9	Grid 7	Grid 8	Grid 9
119.8	131.0	130.7	119.8	131.0	130.7

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
М3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

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Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_2mm step_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m³ Phantom section: H Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/01/2005

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1): Measurement grid: dx=2mm, dy=2mm

Maximum value of Total (measured) = 138.0 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1): Measurement grid: dx=2mm, dy=2mm Maximum value of Total field (slot averaged) = 131.2 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

E in V/m (Time averaged) E in V/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
123.1	138.6	138.6	123.1	138.6	138.6
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
81.4	92.1	91.6	81.4	92.1	91.6
Grid 7	Grid 8	Grid 9	Grid 7	Grid 8	Grid 9
121.3	131.2	131.0	121.3	131.2	131.0

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
М3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

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Date/Time: 14/07/2005 12:43:02 PM

Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_5 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m³ Phantom section: H Dipole Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm Maximum value of Total field (slot averaged) = 0.406 A/m Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged) H in A/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid
0.342	0.359	0.344	0.342	0.359	0.34
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid
0.389	0.406	0.389	0.389	0.406	0.38
Grid 7	Grid 8	Grid 9	Grid 7	Grid 8	Grid
0.363	0.378	0.363	0.363	0.378	0.36

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

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Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_2 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m³ Phantom section: H Dipole Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/12/2004

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/01/2005

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1): Measurement grid: dx=2mm, dy=2mm

Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):

Measurement grid: dx=2mm, dy=2mm Maximum value of Total field (slot averaged) = 0.406 A/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged) H in A/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
0.347	0.361	0.348	0.347	0.361	0.348
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
0.394	0.406	0.391	0.394	0.406	0.391
Grid 7	Grid 8	Grid 9	Grid 7	Grid 8	Grid 9
0.367	0.380	0.365	0.367	0.380	0.365

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

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A.3 RF emissions and ambient noise plots
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Date/Time: 24/03/2009 4:25:02 PM

Test Laboratory: RTS

File Name: <u>HAC_E_GSM850_low_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 824.2 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 70.8 V/m; Power Drift = -0.038 dB

Maximum value of Total (measured) = 56.1 V/m

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dx=5mm, dy=5mm

Maximum value of peak Total field = 165.2 V/m

Probe Modulation Factor = 2.93

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 70.8 V/m; Power Drift = -0.038 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
144.8 M4	158.6 M3	156.5 M3
Grid 4	Grid 5	Grid 6
155.8 M3	165.2 M3	161.4 M3
Grid 7	Grid 8	Grid 9
161.1 M3	164.0 M3	160.1 M3

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF700	CW



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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 24/03/2009 4:32:33 PM

Test Laboratory: RTS

File Name: <u>HAC_E_GSM850_mid_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 836.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 85.6 V/m; Power Drift = -0.078 dB

Maximum value of Total (measured) = 70.9 V/m

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dx=5mm, dy=5mm

Maximum value of peak Total field = 202.3 V/m

Probe Modulation Factor = 2.93

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 85.6 V/m; Power Drift = -0.078 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Teak E-field III V	/111	
Grid 1	Grid 2	Grid 3
170.9 M3	189.4 M3	187.9 M3
Grid 4	Grid 5	Grid 6
187.5 M3	202.3 M3	198.6 M3
Grid 7	Grid 8	Grid 9
199.7 M3	208.6 M3	198.8 M3

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 24/03/2009 4:39:06 PM

Test Laboratory: RTS

File Name: <u>HAC_E_GSM850_high_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 848.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 88.0 V/m; Power Drift = 0.121 dB

Maximum value of Total (measured) = 73.1 V/m

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dx=5mm, dy=5mm

Maximum value of peak Total field = 211.2 V/m

Probe Modulation Factor = 2.93

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 88.0 V/m; Power Drift = 0.121 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
180.0 M3	197.4 M3	192.7 M3
Grid 4	Grid 5	Grid 6
197.1 M3	211.2 M3	204.6 M3
Grid 7	Grid 8	Grid 9
207.6 M3	214.9 M3	205.1 M3

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70	CW



Date/Time: 24/03/2009 5:14:08 PM

Test Laboratory: RTS

File Name: HAC_E_CDMA800_low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: CDMA 800; Frequency: 824.7 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 82.7 V/m; Power Drift = 0.145 dB

Maximum value of Total (measured) = 68.4 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid:

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dx=5mm, dy=5mm

Maximum value of peak Total field = 65.1 V/m

Probe Modulation Factor = 0.960

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 82.7 V/m; Power Drift = 0.145 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
56.5 M4	62.8 M4	62.0 M4
Grid 4	Grid 5	Grid 6
60.5 M4	65.1 M4	64.1 M4
Grid 7	Grid 8	Grid 9
64.0 M4	65.7 M4	64.1 M4

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF700			CW



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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 24/03/2009 5:20:22 PM

Test Laboratory: RTS

File Name: <u>HAC_E_CDMA800_mid_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: CDMA 800; Frequency: 836.52 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 86.9 V/m; Power Drift = -0.109 dB

Maximum value of Total (measured) = 73.1 V/m

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W

dx=5mm, dy=5mm

Maximum value of peak Total field = 68.3 V/m

Probe Modulation Factor = 0.960

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 86.9 V/m; Power Drift = -0.109 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
55.6 M4	61.8 M4	61.2 M4
Grid 4	Grid 5	Grid 6
63.1 M4	67.1 M4	66.0 M4
Grid 7	Grid 8	Grid 9
68.3 M4	70.3 M4	66.5 M4

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 24/03/2009 5:25:31 PM

Test Laboratory: RTS

File Name: <u>HAC_E_CDMA800_high_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: CDMA 800; Frequency: 848.52 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 96.6 V/m; Power Drift = -0.049 dB

Maximum value of Total (measured) = 80.2 V/m

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W

dx=5mm, dy=5mm

Maximum value of peak Total field = 74.3 V/m

Probe Modulation Factor = 0.960

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 96.6 V/m; Power Drift = -0.049 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
61.6 M4	67.6 M4	67.0 M4
Grid 4	Grid 5	Grid 6
68.5 M4	74.3 M4	72.5 M4
Grid 7	Grid 8	Grid 9
73.1 M4	77.1 M4	73.2 M4

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 24/03/2009 4:45:24 PM

Test Laboratory: RTS

File Name: <u>HAC_E_GSM1900_Low_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1850.2 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 16.3 V/m; Power Drift = -0.210 dB

Maximum value of Total (measured) = 24.8 V/m

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dx=5mm, dy=5mm

Maximum value of peak Total field = 67.1 V/m

Probe Modulation Factor = 2.92

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 16.3 V/m; Power Drift = -0.210 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
67.1 M3	58.5 M3	48.6 M3
Grid 4	Grid 5	Grid 6
62.9 M3	58.3 M3	59.9 M3
Grid 7	Grid 8	Grid 9
53.7 M3	71.9 M3	72.3 M3

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 24/03/2009 4:50:48 PM

Test Laboratory: RTS

File Name: HAC_E_GSM1900_mid_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 16.6 V/m; Power Drift = 0.160 dB

Maximum value of Total (measured) = 23.7 V/m

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Daoud Attayi	Mar 20-24, 2009	W		

dx=5mm, dy=5mm

Maximum value of peak Total field = 66.5 V/m

Probe Modulation Factor = 2.92

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 16.6 V/m; Power Drift = 0.160 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
66.5 M3	58.0 M3	54.0 M3
Grid 4	Grid 5	Grid 6
61.9 M3	55.0 M3	56.7 M3
Grid 7	Grid 8	Grid 9

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Daoud Attayi	Mar 20-24, 2009	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			

Date/Time: 24/03/2009 4:57:03 PM

Test Laboratory: RTS

File Name: <u>HAC_E_GSM1900_high_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1909.8 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 18.9 V/m; Power Drift = 0.155 dB

Maximum value of Total (measured) = 23.5 V/m

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dx=5mm, dy=5mm

Maximum value of peak Total field = 64.3 V/m

Probe Modulation Factor = 2.92

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 18.9 V/m; Power Drift = 0.155 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Feak L-field III	v/III	
Grid 1	Grid 2	Grid 3
64.3 M3	58.5 M3	57.3 M3
Grid 4	Grid 5	Grid 6
51.2 M3	57.6 M3	58.6 M3
Grid 7	Grid 8	Grid 9
40.7 M4	68.1 M3	68.6 M3

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Daoud Attayi	Mar 20-24, 2009	W		

Date/Time: 24/03/2009 5:44:20 PM

Test Laboratory: RTS

File Name: <u>HAC_E_CDMA1900_low_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: CDMA 1900; Frequency: 1851.25 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 19.6 V/m; Power Drift = 0.025 dB

Maximum value of Total (measured) = 30.3 V/m

dx=5mm, dy=5mm

Maximum value of peak Total field = 25.4 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 19.6 V/m; Power Drift = 0.025 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
25.4 M4	23.5 M4	21.3 M4
Grid 4	Grid 5	Grid 6
22.9 M4	25.0 M4	25.7 M4
Grid 7 19.3 M4	Grid 8 30.1 M4	Grid 9 30.4 M4

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 24/03/2009 5:50:23 PM

Test Laboratory: RTS

File Name: <u>HAC_E_CDMA1900_mid_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: CDMA 1900; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 19.6 V/m; Power Drift = 0.287 dB

Maximum value of Total (measured) = 28.2 V/m

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dx=5mm, dy=5mm

Maximum value of peak Total field = 25.1 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 19.6 V/m; Power Drift = 0.287 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 2	Grid 3
23.0 M4	22.4 M4
Grid 5	Grid 6
22.8 M4	23.4 M4
Grid 8	Grid 9
28.1 M4	28.2 M4
	Grid 2 23.0 M4 Grid 5 22.8 M4 Grid 8 28.1 M4

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 24/03/2009 5:56:08 PM

Test Laboratory: RTS

File Name: <u>HAC_E_CDMA1900_high_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: CDMA 1900; Frequency: 1908.5 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 08/01/2009

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 20.1 V/m; Power Drift = -0.006 dB

Maximum value of Total (measured) = 24.7 V/m

dx=5mm, dy=5mm

Maximum value of peak Total field = 24.7 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 20.1 V/m; Power Drift = -0.006 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
24.7 M4	22.7 M4	22.0 M4
Grid 4	Grid 5	Grid 6
23.4 M4	21.7 M4	22.3 M4
Grid 7	Grid 8	Grid 9
21.0 M4	24.3 M4	24.8 M4

RTS RIM Testing Services	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCF71CW			Page 144 (180)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70CW	


RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCF71CW				
Author Data	Dates of Test	Report No	FCC ID		
Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W	

Date/Time: 24/03/2009 6:10:10 PM

Test Laboratory: RTS

File Name: HAC_H_GSM850_Low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 824.2 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.110 A/m; Power Drift = -0.048 dB

Maximum value of Total (measured) = 0.152 A/m

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Author Data	Dates of Test	Report No	FCC ID		
Daoud Attayi	Mar 20-24, 2009	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70CV			

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.425 A/m

Probe Modulation Factor = 2.79

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.110 A/m; Power Drift = -0.048 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
0.425 M4	0.347 M4	0.259 M4
Grid 4	Grid 5	Grid 6
0.391 M4	0.319 M4	0.248 M4
Grid 7	Grid 8	Grid 9
0.367 M4	0.278 M4	0.206 M4

RTS RIM Testing Services	Annex A to Hearing Report for the Black	Page 147 (180)		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009	CW		



RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCF71CW			
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 24/03/2009 6:17:55 PM

Test Laboratory: RTS

File Name: <u>HAC_H_GSM850_Mid_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 836.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.123 A/m; Power Drift = 0.135 dB

Maximum value of Total (measured) = 0.169 A/m

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.473 A/m

Probe Modulation Factor = 2.79

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.123 A/m; Power Drift = 0.135 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
0.473 M3	0.378 M4	0.270 M4
Grid 4	Grid 5	Grid 6
0.441 M4	0.354 M4	0.267 M4
Grid 7	Grid 8	Grid 9
0.435 M4	0.326 M4	0.243 M4





 $0 \, dB = 0.473 \text{A/m}$

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Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 24/03/2009 6:23:50 PM

Test Laboratory: RTS

File Name: HAC_H_GSM850_High_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 848.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.125 A/m; Power Drift = -0.051 dB

Maximum value of Total (measured) = 0.185 A/m

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.500 A/m

Probe Modulation Factor = 2.79

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.125 A/m; Power Drift = -0.051 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
0.500 M3	0.381 M4	0.270 M4
Grid 4	Grid 5	Grid 6
0.488 M3	0.373 M4	0.270 M4
		0.10
Grid 7	Grid 8	Grid 9
0.516 M3	0.385 M4	0.260 M4

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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70CV			CW



Date/Time: 24/03/2009 7:11:11 PM

Test Laboratory: RTS

File Name: <u>HAC_H_CDMA850_Low_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: CDMA 800; Frequency: 824.7 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.148 A/m; Power Drift = -0.016 dB

Maximum value of Total (measured) = 0.194 A/m

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.183 A/m

Probe Modulation Factor = 0.940

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.148 A/m; Power Drift = -0.016 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.183 M4	0.154 M4	0.119 M4
Grid 4	Grid 5	Grid 6
0.167 M4	0.141 M4	0.115 M4
Grid 7	Grid 8	Grid 9
0.161 M4	0.124 M4	0.095 M4

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Daoud Attayi	Mar 20-24, 2009	Iar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70CW			



RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCF71CW				
Author Data	Dates of Test	Report No	FCC ID		
Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W	

Date/Time: 24/03/2009 7:20:04 PM

Test Laboratory: RTS

File Name: <u>HAC_H_CDMA850_Mid_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: CDMA 800; Frequency: 836.52 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.146 A/m; Power Drift = -0.099 dB

Maximum value of Total (measured) = 0.172 A/m

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.161 A/m

Probe Modulation Factor = 0.940

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.146 A/m; Power Drift = -0.099 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.161 M4	0.133 M4	0.104 M4
Grid 4	Grid 5	Grid 6
0.150 M4	0.127 M4	0.104 M4
Grid 7	Grid 8	Grid 9
0.149 M4	0.118 M4	0.093 M4

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Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70CV			CW



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Daoud Attayi	Mar 20-24, 2009	W		

Date/Time: 24/03/2009 7:27:17 PM

Test Laboratory: RTS

File Name: <u>HAC_H_CDMA850_High_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: CDMA 800; Frequency: 848.52 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.127 A/m; Power Drift = -0.010 dB

Maximum value of Total (measured) = 0.188 A/m

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Daoud Attayi	Mar 20-24, 2009	W		

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.168 A/m

Probe Modulation Factor = 0.940

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.127 A/m; Power Drift = -0.010 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in	i A/m	
Grid 1	Grid 2	Grid 3
0.168 M4	0.127 M4	0.090 M4
Grid 4	Grid 5	Grid 6
0.165 M4	0.127 M4	0.092 M4
Grid 7	Grid 8	Grid 9
0.177 M4	0.132 M4	0.089 M4

Dool II field in A/r

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCF71CW				
Author Data	Dates of Test	Report No	FCC ID		
Daoud Attayi	Mar 20-24, 2009	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70CW			



Date/Time: 24/03/2009 6:49:52 PM

Test Laboratory: RTS

File Name: HAC_H_GSM1900_Low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1850.2 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.069 A/m; Power Drift = 0.065 dB

Maximum value of Total (measured) = 0.071 A/m

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.179 A/m

Probe Modulation Factor = 2.54

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.069 A/m; Power Drift = 0.065 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
0.179 M3	0.172 M3	0.163 M3
Grid 4	Grid 5	Grid 6
0.160 M3	0.165 M3	0.162 M3
Grid 7	Grid 8	Grid 9
0.178 M3	0.171 M3	0.151 M3

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Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			CW



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Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W

Date/Time: 24/03/2009 6:56:16 PM

Test Laboratory: RTS

File Name: HAC_H_GSM1900_Mid_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.080 A/m; Power Drift = -0.064 dB

Maximum value of Total (measured) = 0.083 A/m

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.212 A/m

Probe Modulation Factor = 2.54

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.080 A/m; Power Drift = -0.064 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
0.212 M3	0.197 M3	0.183 M3
Grid 4	Grid 5	Grid 6
0.180 M3	0.188 M3	0.182 M3
Grid 7	Grid 8	Grid 9
0.175 M3	0.178 M3	0.171 M3

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCF71CW			
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			CW



RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CF71CW	Page 169 (180)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009	W		

Date/Time: 24/03/2009 7:02:08 PM

Test Laboratory: RTS

File Name: <u>HAC_H_GSM1900_High_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1909.8 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.078 A/m; Power Drift = -0.050 dB

Maximum value of Total (measured) = 0.085 A/m

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.216 A/m

Probe Modulation Factor = 2.54

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.078 A/m; Power Drift = -0.050 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Grid 1	Grid 2	Grid 3
0.216 M3	0.208 M3	0.180 M3
Grid 4	Grid 5	Grid 6
0.185 M3	0.187 M3	0.179 M3
Grid 7	Grid 8	Grid 9
0.171 M3	0.173 M3	0.165 M3







RTS RIM Testing Services	Annex A to Hearing Aic Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CF71CW	Page 172 (180)
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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 24/03/2009 7:40:22 PM

Test Laboratory: RTS

File Name: <u>HAC_H_CDMA1900_Low_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: CDMA 1900; Frequency: 1851.25 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.084 A/m; Power Drift = 0.039 dB

Maximum value of Total (measured) = 0.083 A/m

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Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.080 A/m

Probe Modulation Factor = 0.960

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.084 A/m; Power Drift = 0.039 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

reak II-lield III A/	111	
Grid 1	Grid 2	Grid 3
0.080 M4	0.075 M4	0.075 M4
Grid 4	Grid 5	Grid 6
0.071 M4	0.075 M4	0.075 M4
Grid 7	Grid 8	Grid 9
		0 070 M4
0.078 M4	0.074 M4	0.070 1114

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCF71CW			
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C		CW	



RTS RIM Testing Services	Annex A to Hearing Aic Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model RC	ns Test CF71CW	Page 175 (180)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70CV			W

Date/Time: 24/03/2009 7:46:26 PM

Test Laboratory: RTS

File Name: <u>HAC_H_CDMA1900_Mid_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: CDMA 1900; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.087 A/m; Power Drift = -0.021 dB

Maximum value of Total (measured) = 0.092 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCF71CW			
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70C			W

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.088 A/m

Probe Modulation Factor = 0.960

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.087 A/m; Power Drift = -0.021 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3	
0.088 M4	0.083 M4	0.076 M4	
Grid 4	Grid 5	Grid 6	
0.076 M4	0.078 M4	0.076 M4	

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	d Compatibility RF Emissic rry® Smartphone model R(ons Test CF71CW	Page 177 (180)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Aar 20-24, 2009 RTS-1528-0903-38 Rev 1 L6ARCF70CW			



RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CF71CW	Page 178 (180)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

Date/Time: 24/03/2009 7:52:14 PM

Test Laboratory: RTS

File Name: HAC_H_CDMA1900_High_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: CDMA 1900; Frequency: 1908.5 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/11/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/03/2009

- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.083 A/m; Power Drift = -0.138 dB

Maximum value of Total (measured) = 0.092 A/m

RTS RIM Testing Services	Annex A to Hearing A Report for the BlackB	id Compatibility RF Emissio erry® Smartphone model R0	ons Test CF71CW	Page 179 (180)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70C	W

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.089 A/m

Probe Modulation Factor = 0.960

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.083 A/m; Power Drift = -0.138 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3		
0.089 M4	0.086 M4	0.075 M4		
Grid 4	Grid 5	Grid 6		
0.076 M4	0.077 M4	0.073 M4		
Grid 7	Grid 8	Grid 9		
0.069 M4	0.070 M4	0.067 M4		

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCF71CW			Page 180 (180)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Mar 20-24, 2009	RTS-1528-0903-38 Rev 1	L6ARCF70CW	

